## NSN 5961-01-505-1436

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-505-1436 **Inclosure Material:** Metal **Overall Length:** Between 0.232 inches and 0.270 inches **Terminal Length:** 0.500 inches **Overall Diameter:** Between 0.179 inches and 0.187 inches **End Application:** Maintenance recorder unit, tornado **Internal Configuration:** Junction contact **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 50.0 collector to base voltage, dc and 30.0 collector to emitter voltage, dc and 5.0 emitter to base voltage, dc and 5.0 emitter to collector voltage, dc **Current Rating Per Characteristic:** 50.00 milliamperes source cutoff current **Power Rating Per Characteristic:** 250.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Product Name:** Npn silicon phototransistors **Special Features:** Narrow receiving angle; variety of sensitivity ranges **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure:** 

Fiig: A110a0

No

**Demilitarization:**